

ABSTRACT OF THE DISCLOSURE

To provide a liquid crystal device capable of controlling leakage current of a thin-film transistor to an extremely low level, making it easy to achieve extra-high definition of pixels, and to provide electronic equipment having the liquid crystal device, a liquid crystal device includes a TFT of a P-type transistor having a semiconductor layer formed of polysilicon, and a plurality of gate electrodes that intersect with the semiconductor layer at a plurality of locations. The liquid crystal device has an LDD structure in which lightly doped regions are formed on both sides of each channel region of the semiconductor layer. A light shielding device (a light shielding film and a data line branched portion) are provided on both sides in the direction of the thickness of the thin-film transistor.